



Docket No.: M4065.0482/P482
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Terry L. Gilton, et al.

Allowed: August 13, 2003

Application No.: 10/077,784

Confirmation No.: 3635

Filed: February 20, 2002

Art Unit: 2818

For: REMOVABLE PROGRAMMABLE
CONDUCTOR MEMORY CARD AND
ASSOCIATED READ/WRITE DEVICE
AND METHOD OF OPERATION

Examiner: T. Phan

REQUEST TO ACKNOWLEDGE CONSIDERATION OF IDS

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

In reviewing the above-captioned application file upon allowance, Applicants' undersigned has noticed that Applicants' Forms PTO-1449, which accompanied Information Disclosure Statements filed on July 17, 2002, October 8, 2002, and December 5, 2002 have not yet been acknowledged by the Examiner. Copies of the unacknowledged Information Disclosure Statements are attached. The Examiner is

therefore kindly requested to immediately return the initialed forms to the undersigned as soon as possible.

Dated: November 11, 2003
12

Respectfully submitted,

By 

Thomas J. D'Amico, Reg.No.: 28,371

Ryan H. Flax, Reg.No.: 48,141

DICKSTEIN SHAPIRO MORIN &
OSHINSKY LLP

2101 L Street NW

Washington, DC 20037-1526

(202) 785-9700

Attorney for Applicants



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SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT (IDS)

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

Pursuant to 37 C.F.R. §§ 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the references listed on the attached PTO/SB/08. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the references be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

The Director is hereby authorized to charge any deficiency in the fees filed, asserted to be filed or which should have been filed herewith (or with any paper hereafter

filed in this application by this firm) to our Deposit Account No. 04-1073, under Order No. M4065.0482/P482. A duplicate copy of this paper is enclosed.

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Attorney for Applicant



Substitute for form 1449A/PTO				Complete If Known	
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				First Named Inventor	Terry L. Gilton
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				Examiner Name	Not Yet Assigned
Sheet	1	of	1	Attorney Docket Number	M4065.0482/P482

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number Number-Kind Code ³ (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
A		5,883,827	3/16/1999	Morgan	

FOREIGN PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Foreign Patent Document Country Code ⁴ -Number ⁴ -Kind Code ⁵ (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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¹Applicant's unique citation designation number (optional). ²See attached Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the application number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶Applicant is to place a check mark here if English language Translation is attached.

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS					
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		Number-Kind Code ² (if known)			
AA	5,761,115		06/02/1998	Kozicki et al.	
AB	6,084,796		07/04/2000	Kozicki et al.	
AC	5,914,893		06/22/1999	Kozicki et al.	
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AJ	5,789,277		08/04/1998	Zahorik et al.	
AK	6,348,365		02/19/2202	Moore et al.	
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AO					

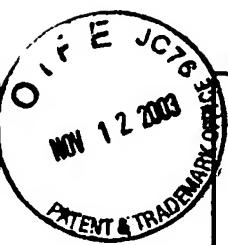
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BA	WO 02/21542		03/14/2002	Kozicki et al.		
BB	WO 00/48196		08/17/2000	Kozicki et al.		
BC	WO 97/48032		12/18/1997	Kozicki et al.		
BD	WO 99/28914		06/10/1999	Kozicki et al.		

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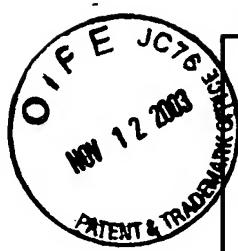
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OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS

Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
CA	Abdel-All, A.; Elshafie, A.; Elhawary, M.M., DC electric-field effect in bulk and thin-film Ge5As38Te57 chalcogenide glass, Vacuum 59 (2000) 845-853.		
CB	Adler, D.; Moss, S.C., Amorphous memories and bistable switches, J. Vac. Sci. Technol. 9 (1972) 1182-1189.		
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CE	Afifi, M.A.; Labib, H.H.; Fouad, S.S.; El-Shazly, A.A., Electrical & thermal conductivity of the amorphous semiconductor GexSe1-x, Egypt, J. Phys. 17 (1986) 335-342.		
CF	Alekperova, Sh.M.; Gadzhieva, G.S., Current-Voltage characteristics of Ag2Se single crystal near the phase transition, Inorganic Materials 23 (1987) 137-139.		
CG	Aleksieunas, A.; Cesnys, A., Switching phenomenon and memory effect in thin-film heterojunction of polycrystalline selenium-silver selenide, Phys. Stat. Sol. (a) 19 (1973) K169-K171.		
CH	Angell, C.A., Mobile ions in amorphous solids, Annu. Rev. Phys. Chem. 43 (1992) 693-717.		
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CJ	Asahara, Y.; Izumitani, T., Voltage controlled switching in Cu-As-Se compositions, J. Non-Cryst. Solids 11 (1972) 97-104.		
CK	Asokan, S.; Prasad, M.V.N.; Parthasarathy, G.; Gopal, E.S.R., Mechanical and chemical thresholds in IV-VI chalcogenide glasses, Phys. Rev. Lett. 62 (1989) 808-810		
CL	Baranovskii, S.D.; Cordes, H., On the conduction mechanism in ionic glasses, J. Chem. Phys. 111 (1999) 7546-7557.		
CM	Belin, R.; Taillades, G.; Pradel, A.; Ribes, M., Ion dynamics in superionic chalcogenide glasses: complete conductivity spectra, Solid state Ionics 136-137 (2000) 1025-1029.		
CN	Belin, R.; Zerouale, A.; Pradel, A.; Ribes, M., Ion dynamics in the argyrodite compound Ag7GeSe5I: non-Arrhenius behavior and complete conductivity spectra, Solid State Ionics 143 (2001) 445-455.		
CO	Benmore, C.J.; Salmon, P.S., Structure of fast ion conducting and semiconducting glassy chalcogenide alloys, Phys. Rev. Lett. 73 (1994) 264-267.		
CP	Benede, J.C., Influence du metal des electrodes sur les caracteristiques courant-tension des structures M-Ag2Se-M, Thin solid films 70 (1980) L1-L4.		
CQ	Benede, J.C., Polarized memory switching in MIS thin films, Thin Solid Films 81 (1981) 155-160.		
CR	Benede, J.C., Switching and silver movements in Ag2Se thin films, Phys. Stat. Sol. (a) 57 (1980) K101-K104.		
CS	Benede, J.C.; Abachi, T., Differential negative resistance in metal/insulator/metal structures with an upper bilayer electrode, Thin solid films 131 (1985) L61-L64.		
CT	Benede, J.C.; Conan, A.; Fousenant, E.; El Bouchairi, B.; Goureaux, G., Polarized memory switching effects in Ag2Se/Se/M thin film sandwiches, Thin solid films 97 (1982) 165-171.		
CU	Benede, J.C.; Khelil, A.; Kettaf, M.; Conan, A., Transition from S- to N-type differential negative resistance in Al-Al2O3-Ag2-xSe1+x thin film structures, Phys. Stat. Sol. (a) 74 (1982) 217-224.		
CV	Bondarev, V.N.; Pikhitsa, P.V., A dendrite model of current instability in RbAg4I5, Solid State Ionics 70/71 (1994) 72-76.		
CW	Boolchand, P., The maximum in glass transition temperature (Tg) near x=1/3 in GexSe1-x		

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First Named Inventor Terry L. Gilton

Group Art Unit 2818

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		Glasses, Asian Journal of Physics (2000) 9, 709-72.	
CX		Boolchand, P.; Bresser, W.J., Mobile silver ions and glass formation in solid electrolytes, Nature 410 (2001) 1070-1073.	
CY		Boolchand, P.; Georgiev, D.G.; Goodman, B., Discovery of the Intermediate Phase in Chalcogenide Glasses, J. Optoelectronics and Advanced Materials, 3 (2001), 703	
CZ		Boolchand, P.; Selvanathan, D.; Wang, Y.; Georgiev, D.G.; Bresser, W.J., Onset of rigidity in steps in chalcogenide glasses, Properties and Applications of Amorphous Materials, M.F. Thorpe and Tichy, L. (eds.) Kluwer Academic Publishers, the Netherlands, 2001, pp. 97-132.	
CA1		Boolchand, P.; Enzweiler, R.N.; Tenhoover, M., Structural ordering of evaporated amorphous chalcogenide alloy films: role of thermal annealing, Diffusion and Defect Data Vol. 53-54 (1987) 415-420.	
CB1		Boolchand, P.; Grothaus, J.; Bresser, W.J.; Suranyi, P., Structural origin of broken chemical order in a GeSe ₂ glass, Phys. Rev. B 25 (1982) 2975-2978.	
CC1		Boolchand, P.; Grothaus, J.; Phillips, J.C., Broken chemical order and phase separation in Ge _x Se _{1-x} glasses, Solid state comm. 45 (1983) 183-185.	
CD1		Boolchand, P., Bresser, W.J., Compositional trends in glass transition temperature (T _g), network connectivity and nanoscale chemical phase separation in chalcogenides, Dept. of ECECS, Univ. Cincinnati (October 28, 1999) 45221-0030.	
CE1		Boolchand, P.; Grothaus, J., Molecular Structure of Melt-Quenched GeSe ₂ and GeS ₂ glasses compared, Proc. Int. Conf. Phys. Semicond. (Eds. Chadi and Harrison) 17 th (1985) 833-36.	
CF1		Bresser, W.; Boolchand, P.; Suranyi, P., Rigidity percolation and molecular clustering in network glasses, Phys. Rev. Lett. 56 (1986) 2493-2496.	
CG1		Bresser, W.J.; Boolchand, P.; Suranyi, P.; de Neufville, J.P., Intrinsically broken chalcogen chemical order in stoichiometric glasses, Journal de Physique 42 (1981) C4-193-C4-196.	
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CI1		Cahen, D.; Gilet, J.-M.; Schmitz, C.; Chernyak, L.; Gartsman, K.; Jakubowicz, A., Room-Temperature, electric field induced creation of stable devices in CuInSe ₂ Crystals, Science 258 (1992) 271-274.	
CJ1		Chatterjee, R.; Asokan, S.; Titus, S.S.K., Current-controlled negative-resistance behavior and memory switching in bulk As-Te-Se glasses, J. Phys. D: Appl. Phys. 27 (1994) 2624-2627.	
CK1		Chen, C.H.; Tai, K.L., Whisker growth induced by Ag photodoping in glassy Ge _x Se _{1-x} films, Appl. Phys. Lett. 37 (1980) 1075-1077.	
CL1		Chen, G.; Cheng, J., Role of nitrogen in the crystallization of silicon nitride-doped chalcogenide glasses, J. Am. Ceram. Soc. 82 (1999) 2934-2936.	
CM1		Chen, G.; Cheng, J.; Chen, W., Effect of Si ₃ N ₄ on chemical durability of chalcogenide glass, J. Non-Cryst. Solids 220 (1997) 249-253.	
CN1		Cohen, M.H.; Neale, R.G.; Paskin, A., A model for an amorphous semiconductor memory device, J. Non-Cryst. Solids 8-10 (1972) 885-891.	
CO1		Croitoru, N.; Lazarescu, M.; Popescu, C.; Telnici, M.; and Vescan, L., Ohmic and non-ohmic conduction in some amorphous semiconductors, J. Non-Cryst. Solids 8-10 (1972) 781-786.	
CP1		Dalven, R.; Gill, R., Electrical properties of beta-Ag ₂ Te and beta-Ag ₂ Se from 4.2 to 300K, J. Appl. Phys. 38 (1967) 753-756.	
CQ1		Davies, E.A., Semiconductors without form, Search 1 (1970) 152-155.	
CR1		Deamaley, G.; Stoneham, A.M.; Morgan, D.V., Electrical phenomena in amorphous oxide films, Rep. Prog. Phys. 33 (1970) 1129-1191.	
CS1		Dejus, R.J.; Susman, S.; Volin, K.J.; Montague, D.G.; Price, D.L., Structure of Vitreous Ag-Ge-Se, J. Non-Cryst. Solids 143 (1992) 162-180.	
CT1		den Boer, W., Threshold switching in hydrogenated amorphous silicon, Appl. Phys. Lett. 40 (1982) 812-813.	
CU1		Drusdau, T.P.; Panckow, A.N.; Klabunde, F., The hydrogenated amorphous	



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	silicon/nanodisperse metal (SIMAL) system-Films of unique electronic properties, J. Non-Cryst. Solids 198-200 (1996) 829-832.	
CV1	El Bouchairi, B.; Bernede, J.C.; Burgaud, P., Properties of Ag _{2-x} Se _{1+x} /n-Si diodes, Thin Solid Films 110 (1983) 107-113.	
CW1	El Gharras, Z.; Bourahla, A.; Vautier, C., Role of photoinduced defects in amorphous Ge _x Se _{1-x} photoconductivity, J. Non-Cryst. Solids 155 (1993) 171-179.	
CX1	El Ghrandi, R.; Calas, J.; Galibert, G.; Averous, M., Silver photodissolution in amorphous chalcogenide thin films, Thin Solid Films 218 (1992) 259-273.	
CY1	El Ghrandi, R.; Calas, J.; Galibert, G., Ag dissolution kinetics in amorphous GeSe _{5.5} thin films from "in-situ" resistance measurements vs time, Phys. Stat. Sol. (a) 123 (1991) 451-460.	
CZ1	El-kady, Y.L., The threshold switching in semiconducting glass Ge ₂₁ Se ₁₇ Te ₆₂ , Indian J. Phys. 70A (1996) 507-516.	
CA2	Elliott, S.R., A unified mechanism for metal photodissolution in amorphous chalcogenide materials, J. Non-Cryst. Solids 130 (1991) 85-97.	
CB2	Elliott, S.R., Photodissolution of metals in chalcogenide glasses: A unified mechanism, J. Non-Cryst. Solids 137-138 (1991) 1031-1034.	
CC2	Elsamanoudy, M.M.; Hegab, N.A.; Fadel, M., Conduction mechanism in the pre-switching state of thin films containing Te As Ge Si, Vacuum 46 (1995) 701-707.	
CD2	El-Zahed, H.; El-Korashy, A., Influence of composition on the electrical and optical properties of Ge ₂₀ BixSe _{80-x} films, Thin Solid Films 376 (2000) 236-240.	
CE2	Fadel, M., Switching phenomenon in evaporated Se-Ge-As thin films of amorphous chalcogenide glass, Vacuum 44 (1993) 851-855.	
CF2	Fadel, M.; El-Shair, H.T., Electrical, thermal and optical properties of Se ₇₅ Ge ₇ Sb ₁₈ , Vacuum 43 (1992) 253-257.	
CG2	Feng, X.; Bresser, W.J.; Boolchand, P., Direct evidence for stiffness threshold in Chalcogenide glasses, Phys. Rev. Lett. 78 (1997) 4422-4425.	
CH2	Feng, X.; Bresser, W.J.; Zhang, M.; Goodman, B.; Boolchand, P., Role of network connectivity on the elastic, plastic and thermal behavior of covalent glasses, J. Non-Cryst. Solids 222 (1997) 137-143.	
CI2	Fischer-Colbrie, A.; Bienenstock, A.; Fuoss, P.H.; Marcus, M.A., Structure and bonding in photodiffused amorphous Ag-GeSe ₂ thin films, Phys. Rev. B 38 (1988) 12388-12403.	
CJ2	Fleury, G.; Hamou, A.; Viger, C.; Vautier, C., Conductivity and crystallization of amorphous selenium, Phys. Stat. Sol. (a) 64 (1981) 311-316.	
CK2	Fritzsche, H., Optical and electrical energy gaps in amorphous semiconductors, J. Non-Cryst. Solids 6 (1971) 49-71.	
CL2	Fritzsche, H., Electronic phenomena in amorphous semiconductors, Annual Review of Materials Science 2 (1972) 697-744.	
CM2	Gates, B.; Wu, Y.; Yin, Y.; Yang, P.; Xia, Y., Single-crystalline nanowires of Ag ₂ Se can be synthesized by templating against nanowires of trigonal Se, J. Am. Chem. Soc. (2001) currently ASAP.	
CN2	Gosain, D.P.; Nakamura, M.; Shimizu, T.; Suzuki, M.; Okano, S., Nonvolatile memory based on reversible phase transition phenomena in telluride glasses, Jap. J. Appl. Phys. 28 (1989) 1013-1018.	
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CP2	Guin, J.-P.; Rouxel, T.; Sangleboeuf, J.-C.; Melscoet, I.; Lucas, J., Hardness, toughness, and scratchability of germanium-selenium chalcogenide glasses, J. Am. Ceram. Soc. 85 (2002) 1545-52.	
CQ2	Gupta, Y.P., On electrical switching and memory effects in amorphous chalcogenides, J. Non-Cryst. Sol. 3 (1970) 148-154.	

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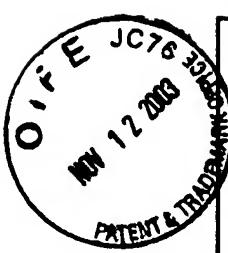
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Sheet	5	of	8	Attorney Docket Number	M4065.0482/P482
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	CR2	Haberland, D.R.; Stiegler, H., New experiments on the charge-controlled switching effect in amorphous semiconductors, <i>J. Non-Cryst. Solids</i> 8-10 (1972) 408-414.	
	CS2	Haifz, M.M.; Ibrahim, M.M.; Dongol, M.; Hammad, F.H., Effect of composition on the structure and electrical properties of As-Se-Cu glasses, <i>J. Appl. Phys.</i> 54 (1983) 1950-1954.	
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	CW2	Hajto, J.; Owen, A.E.; Snell, A.J.; Le Comber, P.G.; Rose, M.J., Analogue memory and ballistic electron effects in metal-amorphous silicon structures, <i>Phil. Mag. B</i> 63 (1991) 349-369.	
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	CZ2	Hirose, Y.; Hirose, H., Polarity-dependent memory switching and behavior of Ag dendrite in Ag-photodoped amorphous As ₂ S ₃ films, <i>J. Appl. Phys.</i> 47 (1976) 2767-2772.	
	CA3	Hong, K.S.; Speyer, R.F., Switching behavior in II-IV-V ₂ amorphous semiconductor systems, <i>J. Non-Cryst. Solids</i> 116 (1990) 191-200.	
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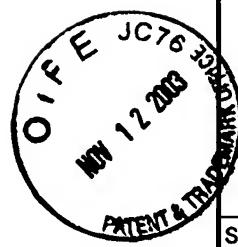
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Filing Date	February 20, 2002
First Named Inventor	Terry L. Gilton
Group Art Unit	2818
Examiner Name	Not Yet Assigned

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				Application Number	10/077,784
				Filing Date	February 20, 2002
				First Named Inventor	Gilton, et al.
				Art Unit	2818
				Examiner Name	T. Phan
Sheet	1	of	4	Attorney Docket Number	M4065.0482/P482

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		Number-Kind Code ² (if known)			
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				Examiner Name	T. Phan
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PTO/SB/08A (10-01)

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First Named Inventor	Gilton, et al.				
Art Unit	2818				
Examiner Name	T. Phan				
Sheet	3	of	4	Attorney Docket Number	M4065.0482/P482

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)				
BA		56126916	10/19981	Akira et al.		
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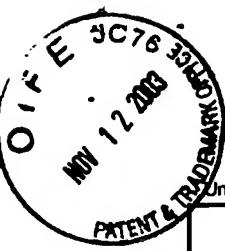
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OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS		
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				Examiner Name	Not Yet Assigned
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Atty Docket No.: M4065.0482/P482

Inventor: Terry L. Gilton, et al.

Application No.: 10/077,784

Filing Date: February 20, 2002

Title: REMOVABLE PROGRAMMABLE CONDUCTOR MEMORY CARD
AND ASSOCIATED READ/WRITE DEVICE
AND METHOD OF OPERATION

Documents Filed:

Preliminary Amendment (4 pages)

IDS Citation (1 page) w/copy of references

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